

Amendments to the Specification:

1. Please replace paragraph [0037] with the following amended paragraph:

[0037] Figure 2 is a cross-sectional view of a wafer 20 made of a semiconducting material, for example silicon. One of its main faces has been treated to make electronic components. Figure 2 is a partial view showing three complete or incomplete components 21. Due to the presence of these components, ~~that~~ the treated plane face has a large relief with several areas of different heights and different roughnesses. When the wafer comprises complete components, part of this relief corresponds to the presence of openings used to connect to electrical contacts.

2. Please replace paragraph [0040] with the following amended paragraph:

[0040] Solidarisation (or bonding) is done by direct wafer bonding, consequently there is no added material at the interface of the two solidarised parts. The total thickness of the bonded parts is not changed and thinning can be done very precisely. This precision then depends on the equipment used. If mechanical thinning is done, a precision of plus or minus ~~+ or less +~~ μm can be obtained.

3. Please replace paragraph [0048] with the following amended paragraph:

[0048] Once the component(s) is (are) transferred onto its (their) final support or onto another intermediate support, it must be possible to separate the component(s) from its (their) part of the support handle. Figure 3E shows a component 21 transferred onto its final support 25, the component 21 still ~~being~~ fixed to its part of the support handle 10. Figure 3F shows the component 21 fixed on its final support 25 and separated from its part of the support handle 10. Separation may be done by any mechanical or pneumatic means used by itself or in combination. For example there is separation by insertion of a tool (Teflon® blade, metallic), by injection of a gas flow, applying a tension and / or shear force.